

HAT2179R

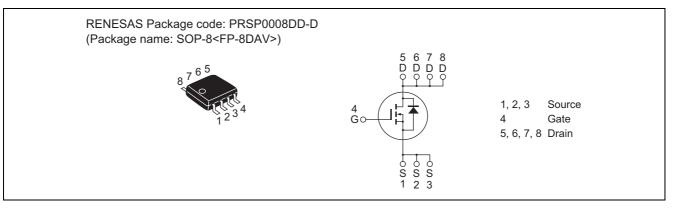
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1570-0100 Rev.1.00 Jul 06, 2007

Features

- Low on-resistance
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$ Symbol Ratings Unit Item 600 Drain to source voltage V_{DSS} V V Gate to source voltage V_{GSS} ±30 Drain current 0.7 A I_D Note1 Drain peak current I_{D (pulse)} 2.0 А Body-drain diode reverse drain current I_{DR} 0.7 A Note Body-drain diode reverse drain peak current IDR (pulse) 2.0 A Pch Note2 Channel dissipation 2.5 W Channel temperature 150 °C Tch Storage temperature Tstg -55 to +150 °C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10 s

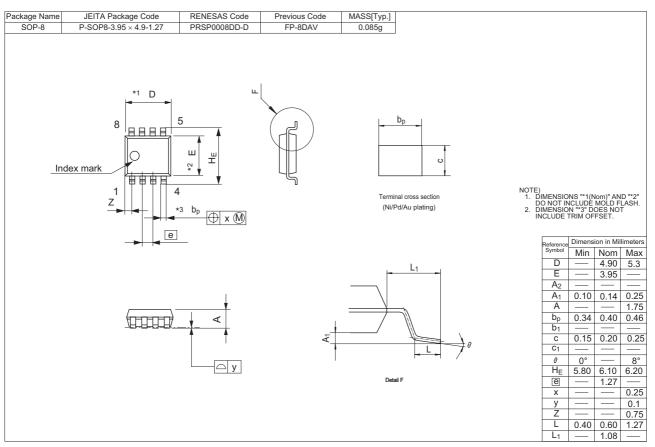
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0		5.0	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Forward transfer admittance	yfs	0.8	1.2	—	S	$I_D = 0.4 \text{ A}, V_{DS} = 10 \text{ V}^{Note3}$
Static drain to source on state	R _{DS(on)}	_	3.5	4.5	Ω	$I_D = 0.4 \text{ A}, V_{GS} = 10 \text{ V}^{Note3}$
resistance						
Input capacitance	Ciss		280	—	pF	V _{DS} = 25 V
Output capacitance	Coss		31	—	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss		3.8	—	pF	
Turn-on delay time	t _{d(on)}	_	24	—	ns	I _D = 0.4 A
Rise time	tr		15	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}		50	_	ns	$R_L = 750 \Omega$
Fall time	t _f	_	58	—	ns	Rg = 10 Ω
Total gate charge	Qg	_	10	—	nC	V _{DD} = 480 V
Gate to source charge	Qgs	_	1.6	—	nC	V _{GS} = 10 V I _D = 0.7 A
Gate to drain charge	Qgd		5.4	_	nC	
Body-drain diode forward voltage	V_{DF}	_	0.8	1.2	V	$I_F = 0.7 \text{ A}, V_{GS} = 0^{Note3}$
Body-drain diode reverse	t _{rr}	_	200	_	ns	$I_F = 0.7 \text{ A}, V_{GS} = 0$
recovery time						di _F /dt = 100 A/µs

Notes: 3. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
HAT2179R-EL-E	2500 pcs	Taping

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